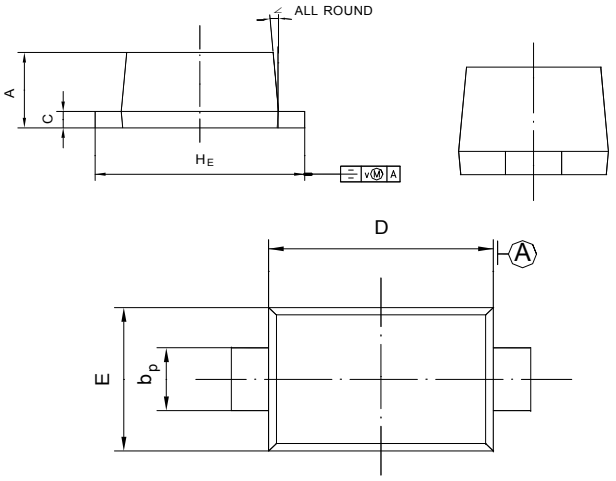
RB751S-40

SCHOTTKY BARRIER DIODE

Features

- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability

Marking Code: " **D** "



UNIT	A	b_p	C	D	E	H_E	V	∠
mm	0.70 0.50	0.40 0.20	0.14 0.05	1.30 1.10	0.90 0.75	1.70 1.50	0.1	5°

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	40	V
Reverse Voltage	V_R	30	V
Mean Rectifying Current	I_O	30	mA
Peak Forward Surge Current (60 Hz, 1 Cycle)	I_{FSM}	200	mA
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	- 40 to + 125	°C

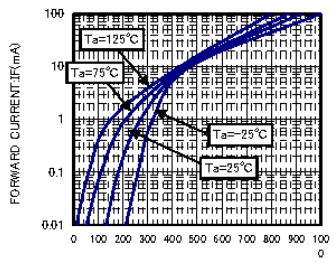
RB751S-40

Characteristics at T_a = 25 °C

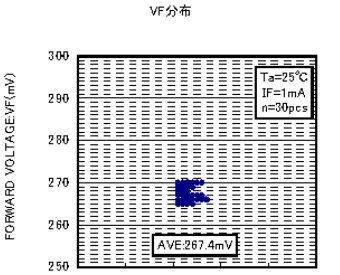
Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at I_F = 1 mA	V_F	-	0.37	V
Reverse Current at V_R = 30 V	I_R	-	0.5	µA
Capacitance Between Terminals at V_R = 1 V, f = 1 MHz	C_T	2	-	pF

Note: ESD sensitive product handling required.

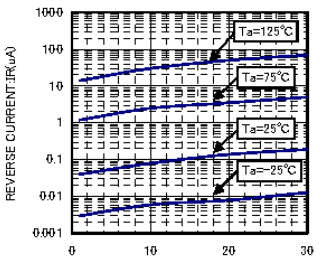
RATING AND CHARACTERISTIC CURVES (RB751S-40)



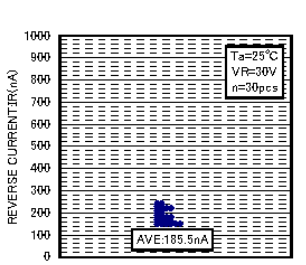
FORWARD VOLTAGE:VF(mV)
VF-IF CHARACTERISTICS

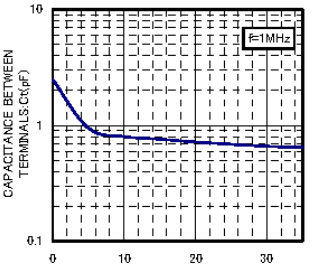


VF分布

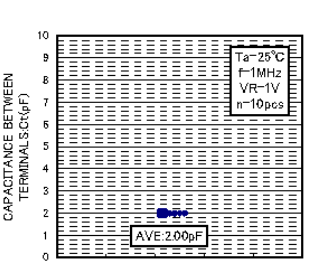


REVERSE VOLTAGE:VR(V)
VR-IR CHARACTERISTICS





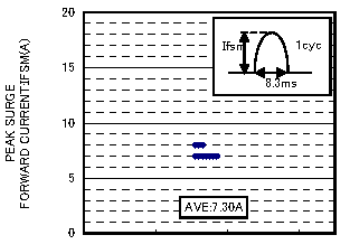
REVERSE VOLTAGE:VR(V)
VR-Ct CHARACTERISTICS



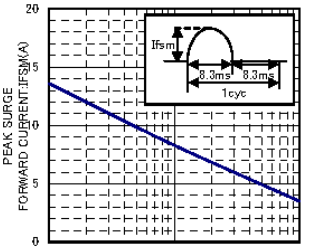
VF DIPERSION MAP

IR DISPERSION MAP

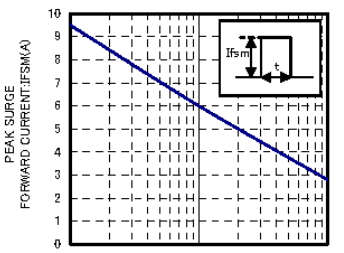
Ct DISPERSION MAP



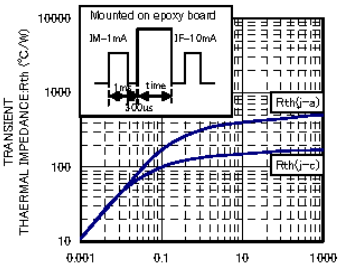
IFSM DISPERSION MAP



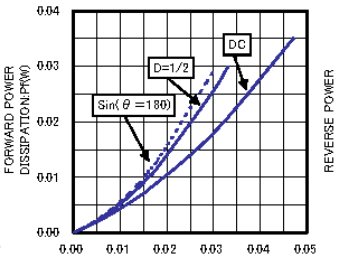
NUMBER OF CYCLES
IFSM-CYCLE CHARACTERISTICS



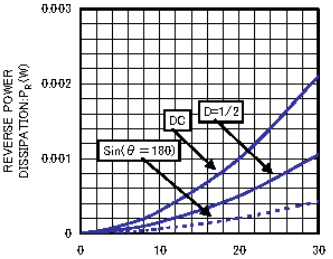
TIME:t(ms)
IFSM-t CHARACTERISTICS



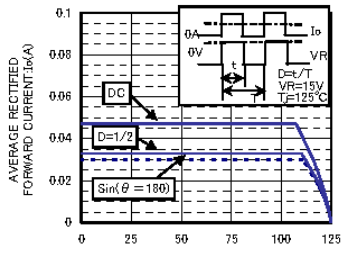
TIME:t(s)
Rth-t CHARACTERISTICS



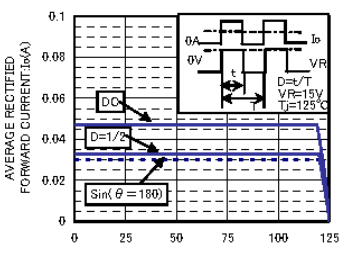
AVERAGE RECTIFIED
FORWARD CURRENT Io(A)
Io-Pf CHARACTERISTICS



REVERSE VOLTAGE:VR(V)
VR-P_R CHARACTERISTICS



AMBIENT TEMPERATURE:Ta(℃)
Derating Curve (Io-Ta)



CASE TEMPARATURE:Tc(℃)
Derating Curve (Io-Tc)